

# Impedance Evaluation of the PF In-Vacuum Undulator: Theory, Simulations, and Measurements

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# Introduction

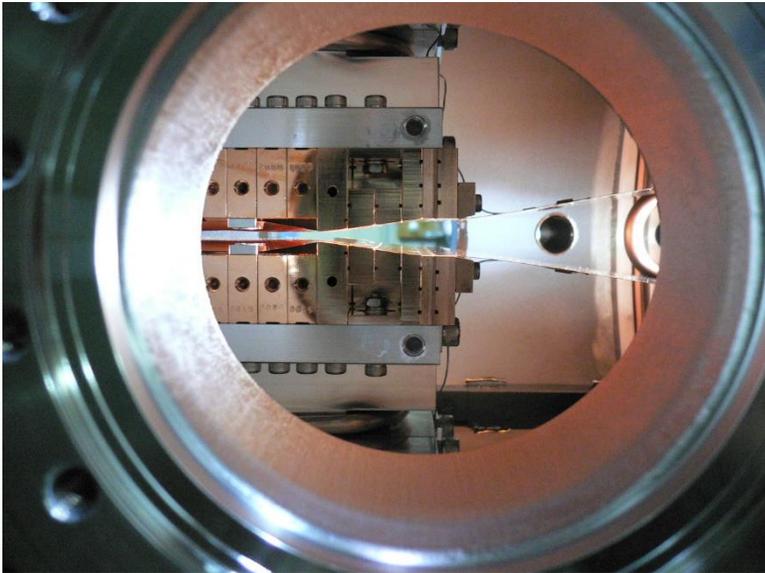
## Motivation

- Four In-Vacuum Undulators (IVU) have been installed to PF recently
- They have RF shields using the standard design to reduce the impedance significantly
- These IVUs were installed to PF long after the construction of the ring itself was completed, and there was a need of the proper IVU's impedance evaluations
- The KEK future light source (KEK - LS) will include one IVU for each DQBA lattice cell (many IVUs are planned to be installed). Evaluation and improvement of their impedance is one more target of the present study
- This talk shows how we identify the major impedance contributors and evaluate their impedance using theoretical formulas, CST Studio simulations and measurements

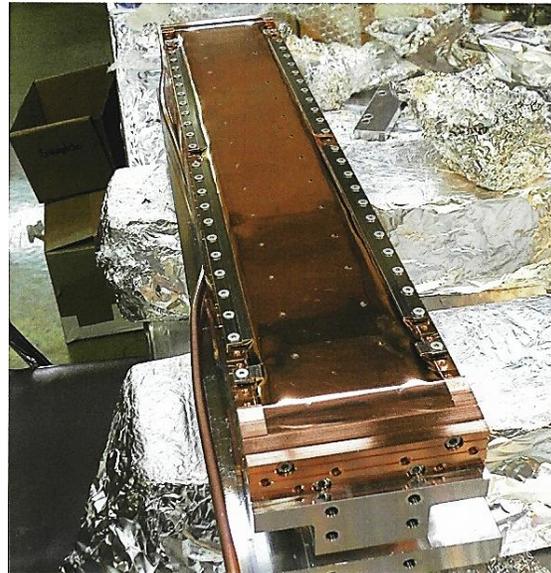
# Introduction

What is PF IVU?

- Three major impedance contributors of PF IVU:



1. Taper between the flange and the undulator (200  $\mu\text{m}$  thick) for the geometrical impedance



2. Copper plate (60  $\mu\text{m}$  copper and 25  $\mu\text{m}$  nickel coating) on top of the undulator for the resistive-wall impedance

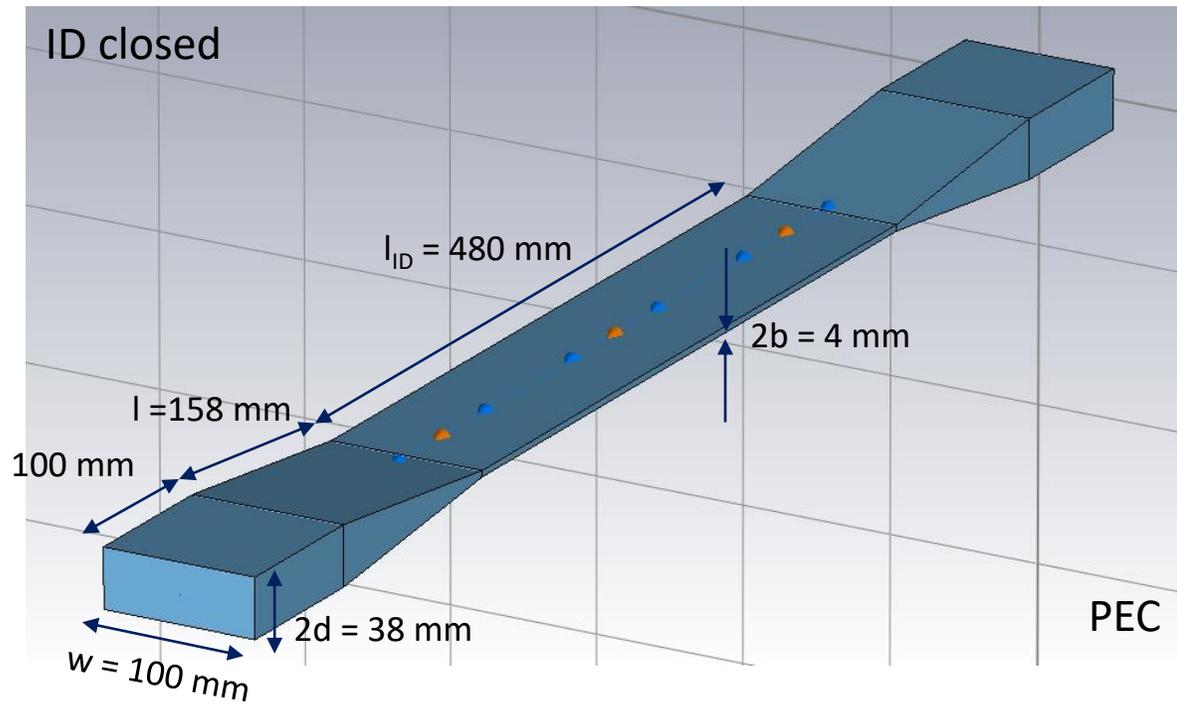


3. Step transition from the octagon to the rectangular chambers

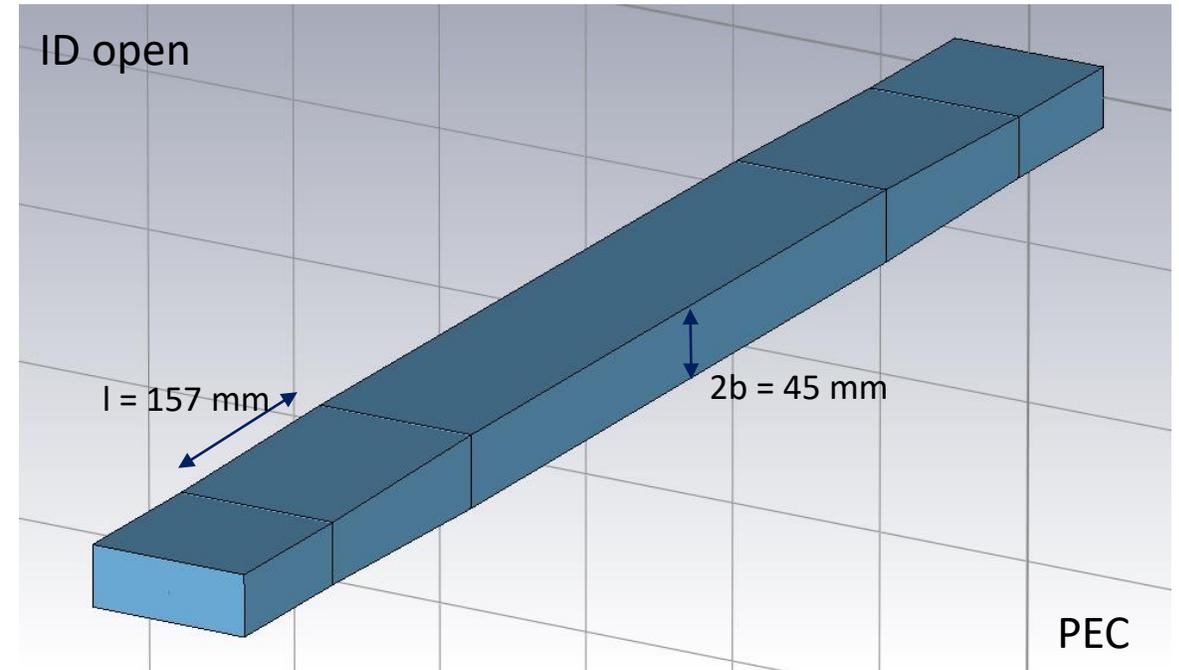
# Introduction

## CST Studio Models of PF IVU

IVU Closed



IVU Open



# 1. Impedance Theory: Verification with Diamond IVU

# 1. Impedance Theory

## Longitudinal Geometrical Impedance of Taper

- The taper structure is known to produce nearly pure inductive impedance even with a vessel included

$$Z_L = -i\omega L$$

$$W_{L0}(s) = Lc \frac{d}{ds} \delta(s/c)$$

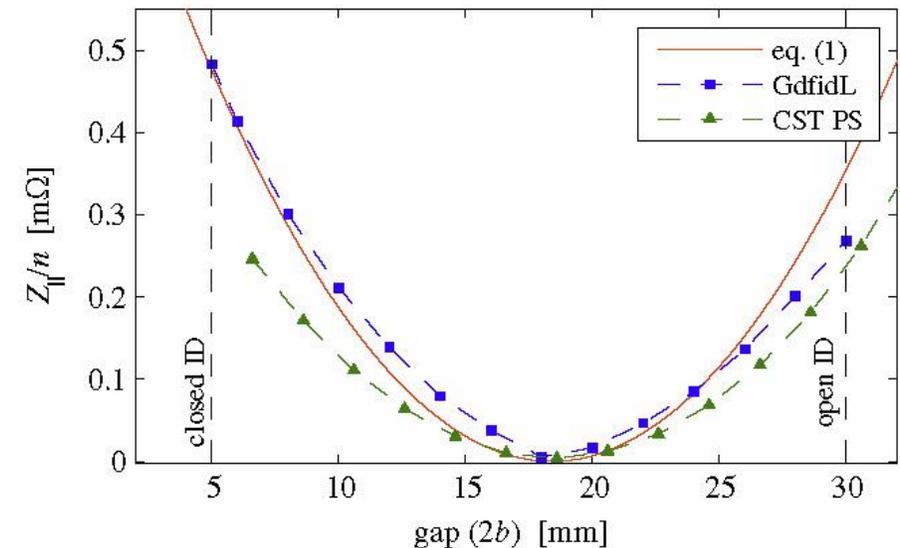
- Theoretical formula for **longitudinal impedance**

$$b \ll w \ll l \quad \frac{Z_l}{n} = -i \frac{Z_0 \omega_0}{4\pi c} \int_{-\infty}^{\infty} (g')^2 F\left(\frac{g}{w}\right) dz,$$

$$F(x) = \sum_{m=0}^{\infty} \frac{1}{2m+1} \operatorname{sech}^2\left((2m+1)\frac{\pi x}{2}\right) \tanh\left((2m+1)\frac{\pi x}{2}\right).$$

G. Stupakov, Phys. Rev. ST Accel. Beams 10, 094401 (2007)

Diamond IVU



V. Smaluk, Phys. Rev. ST Accel. Beams 17, 074402 (2014)

# 1. Impedance Theory

## Transverse Geometrical Impedance of Taper (I)

- We need a careful treatment of the transverse impedance, since **it includes both the dipolar and the quadrupolar components**:

$$W_{y,tot}(y_1, y_2, z) = W_{y,dip}(z)y_1 + W_{y,quad}(z)y_2$$

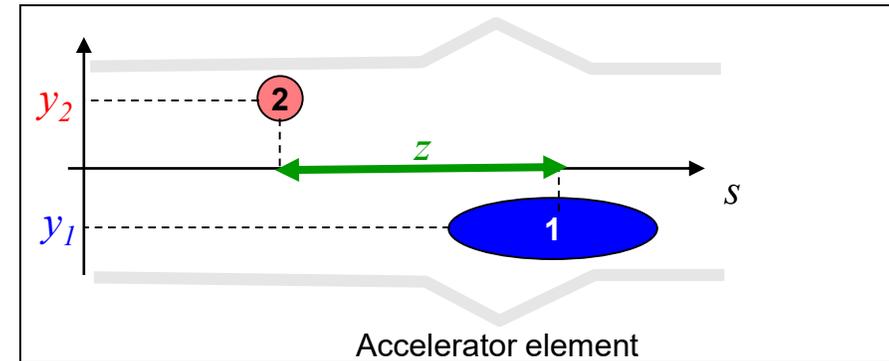
Total wake      Dipolar wake      Quadrupolar wake

B. Salvant, Beam physics for FAIR

- They produce vertical kick factors

$$k_y = \frac{\text{Im } Z_y c}{2\sqrt{\pi}\sigma_z}$$

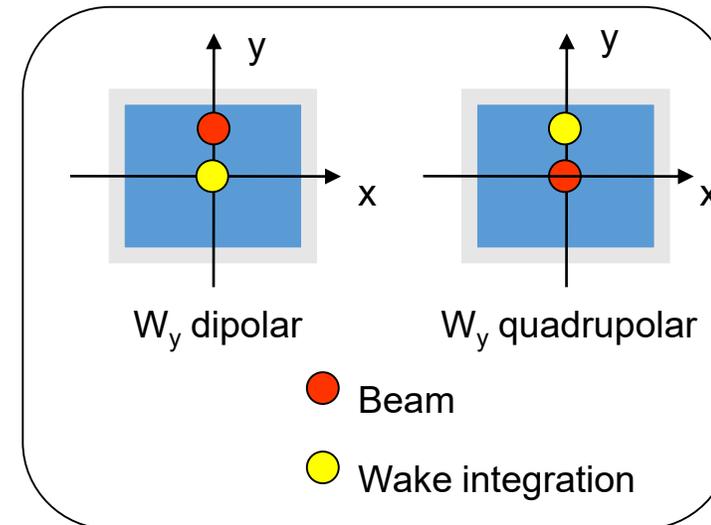
- **Transversely, the calculation of kick factors is most important since it provides additional coherent vertical tune shift**



# 1. Impedance Theory

Dipolar, Quadrupolar?

- In asymmetric structures, they are different concepts from dipole and quadrupole modes
- They can be calculated by displacing the beam and the wake integration path separately
- Machine measurements
  - Tune shift
    - dipolar + quadrupolar
  - Instability growth rate
    - dipolar



B. Salvant, Beam physics for FAIR

# 1. Impedance Theory

## Transverse Geometrical Impedance of Taper (II)

- Theoretical formula for **dipolar impedance**

$$Z_{yD}(k) = -i \frac{Z_0}{2\pi b} \int_{-\infty}^{\infty} \frac{\xi^2}{\sinh^2 \xi} \sum_{n=0}^{\infty} \delta_n \frac{H(k_n, k) + H(k_n, -k)}{2ik_n b} d\xi$$

$$H(p, k) = \int_{-\infty}^{\infty} \int_{-\infty}^{z_1} S'(z_1) S'(z_2) e^{i(p+k)(z_1-z_2)} dz_1 dz_2, \quad k_n b = \sqrt{(kb)^2 - \xi^2 - (\pi n)^2}$$

S. Krinsky, Phys. Rev. ST Accel. Beams 8, 124403 (2005)  $w \rightarrow \infty$

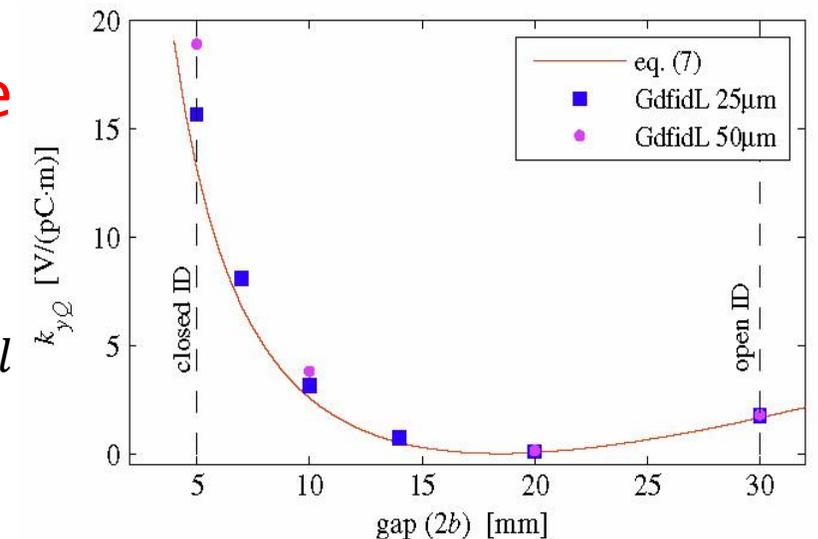
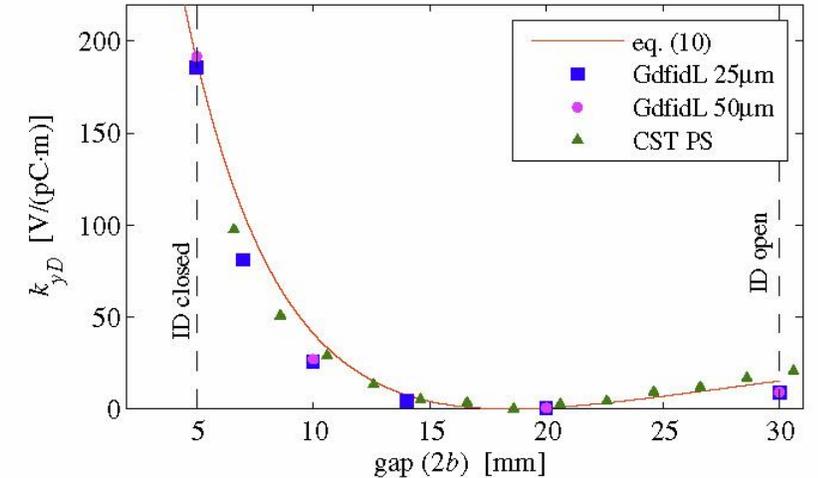
- Theoretical formula for **quadrupolar impedance**

$$Z_{yQ} = -i \frac{\pi Z_0}{4} \int_{-\infty}^{\infty} \frac{(g')^2}{g^2} G\left(\frac{g}{w}\right) dz,$$

$$G(x) = x^2 \sum_{m=0}^{\infty} (2m+1) \times \operatorname{sech}^2\left((2m+1)\frac{\pi x}{2}\right) \tanh\left((2m+1)\frac{\pi x}{2}\right). \quad b \ll w \ll l$$

G. Stupakov, Phys. Rev. ST Accel. Beams 10, 094401 (2007)

Diamond IVU



# 1. Impedance Theory

## Resistive-Wall Impedance of Undulator\*

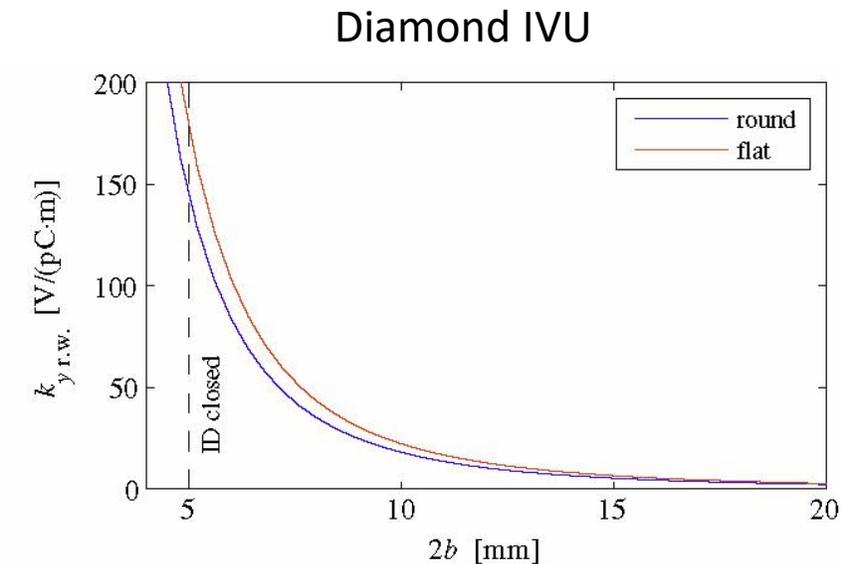
- Transverse impedance per unit length for a vertically displaced beam in a **round chamber** is

$$Z_y^{rnd}(\omega) = \frac{\text{sign}(\omega) + i}{\pi b^3} \sqrt{\frac{c\mu_r Z_0}{2\omega\sigma_c}} \frac{1 + 3(y/b)^2}{\left[1 + 3(y/b)^2\right]^3}$$

- Formula of resistive-wall impedance for a **flat chamber** formed by two infinitely wide plates

$$Z_y^{flat}(\omega) = \pi \frac{\text{sign}(\omega) + i}{8b^3} \sqrt{\frac{c\mu_r Z_0}{2\omega\sigma_c}} \frac{1 + \frac{\pi y}{2b} \tan\left(\frac{\pi y}{2b}\right)}{\cos^2\left(\frac{\pi y}{2b}\right)} \quad Z_y^{flat}(\omega) = \frac{\pi^2}{8} Z_y^{rnd}(\omega)$$

A. Piwinski, Report No. DESY-94-068, Hamburg, 1994.



\* RF shielded by Cu plate

# 1. Impedance Theory

## Geometrical Impedance of Step Transition

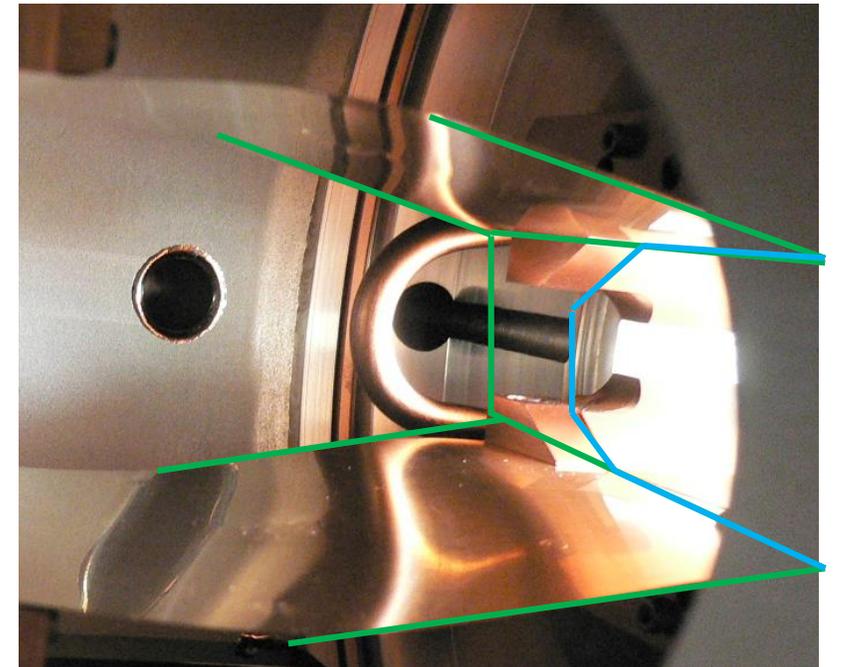
- Low-frequency impedance of the **step transition** at the beginning of the taper can be roughly estimated using formula:

$$Z_y = i \frac{Z_0(d-b)}{\pi b^2} \frac{d^2 - b^2}{d^2 + b^2}$$

- Its power loss will be taken care by the cooling channel in the present design



PF IVU



# 1. Impedance Theory

## Summary

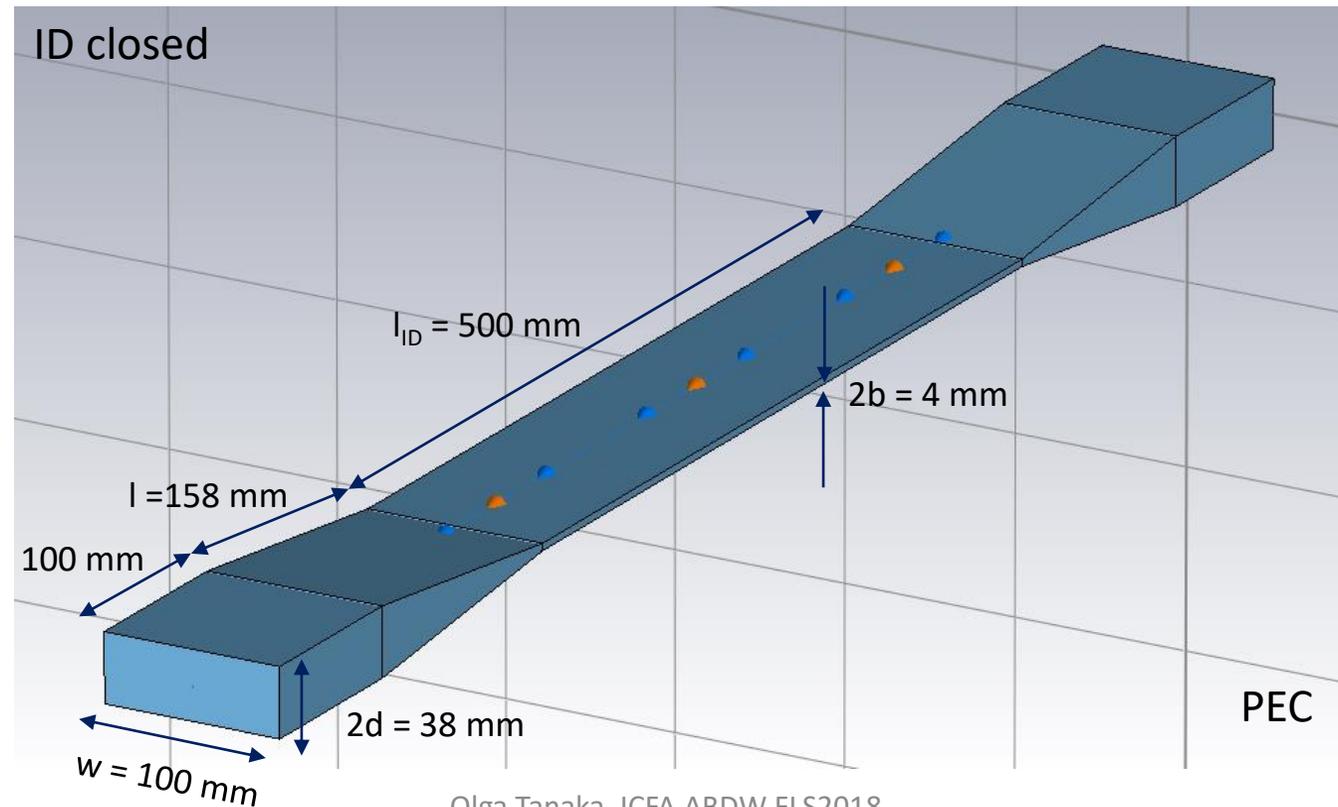
- There are the **analytical formulas** accurate enough for impedance calculations of all the 3 parts of IVU discussed above (geometrical impedance of the taper, resistive-wall impedance of the copper shield, and geometrical impedance of step transition between rectangular and octagonal beam chambers)
- PF IVUs follow the standard design, therefore we can apply the procedure outlined by Smaluk (Phys. Rev. ST Accel. Beams 17, 074402 (2014)) for the impedance evaluation plus some new formulas.
- **The method is to calculate impedance of each part separately using CST and GdfidL and to compare it with the theoretical formula at each time**

## 2. Impedance Evaluation for PF IVU by Simulations and Theory

## 2. Impedance Evaluation for PF IVU

### Taper CST Model

- To calculate **the pure geometrical impedance of the taper**, we first assume the perfectly conductive material instead of using copper resistivity



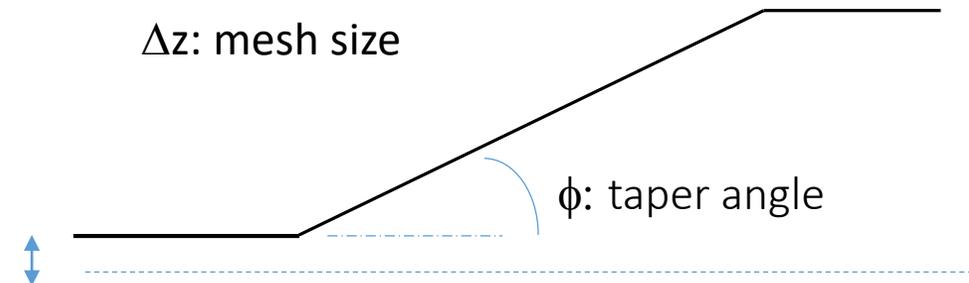
# 2. Impedance Evaluation for PF IVU

## CST Studio Mesh Size

- It is known that a very fine mesh is needed for accurate calculations of the taper impedance
- The empirical formula

$$100 \leq \frac{a\phi}{\Delta z} \cdot \frac{\sigma_z}{\Delta z}$$

a: chamber radius



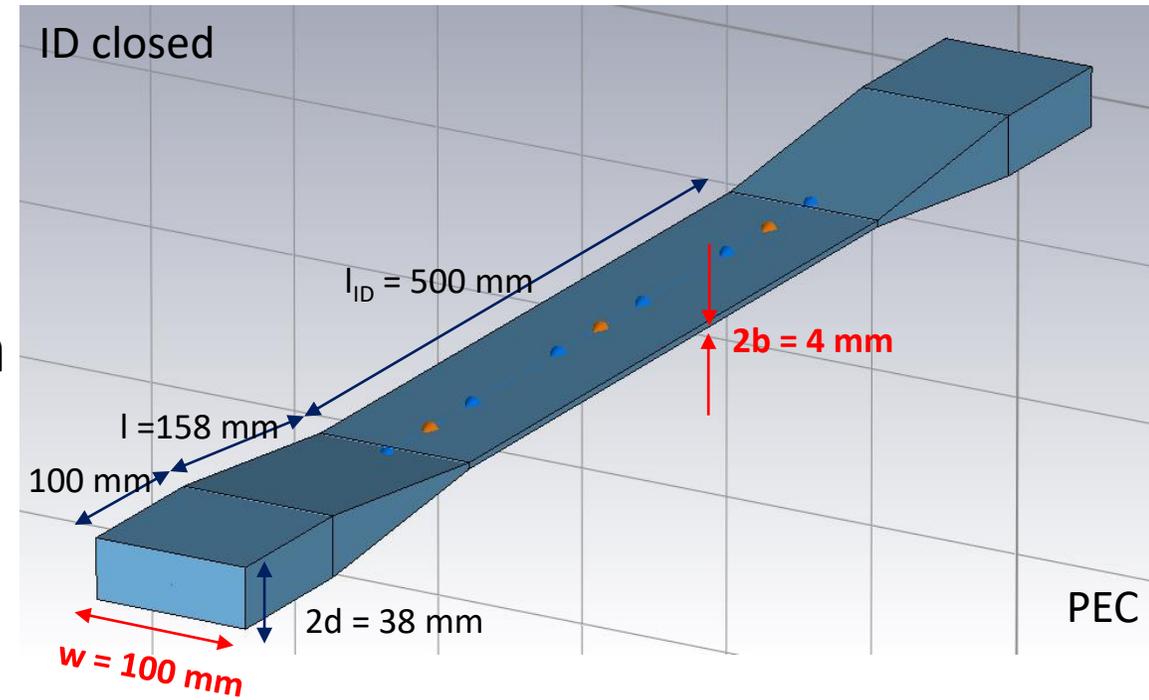
- **We need  $\Delta z < 150 \mu\text{m}$**

Frasciello's slide at SIF2014  
on wakes of LHC collimators

# 2. Impedance Evaluation for PF IVU

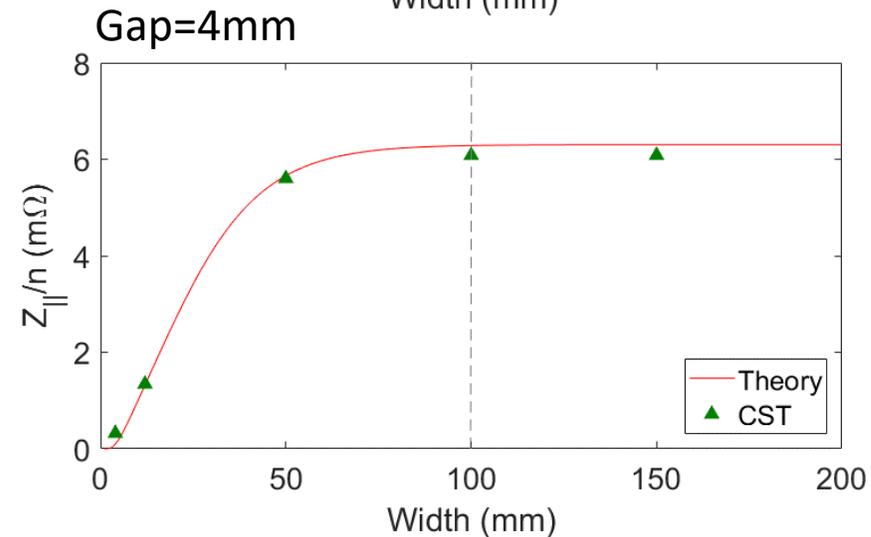
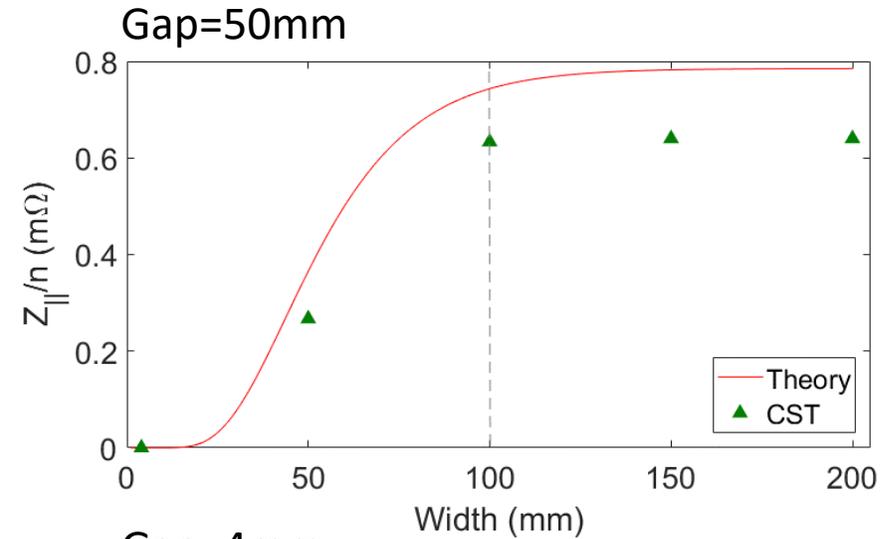
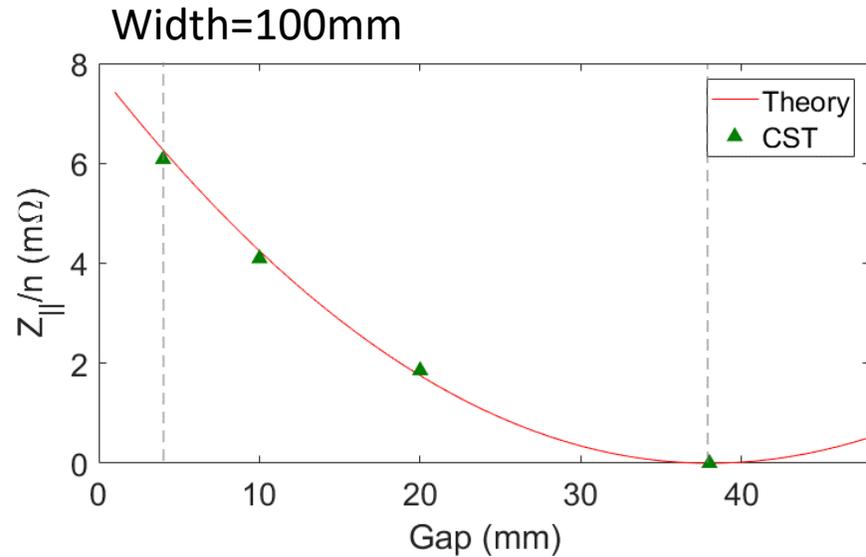
## Parameter Scan

- IVU impedance affected greatly by the **size of its gap**. When ID is closed the difference even in 0.5 mm yields a drastic increase of impedance
- For a better and more economical design in future, we also studied the dependence of kick factors on the **taper width**. Conclusion before the results are shown: **the present 100 mm is reasonable and close to optimal width**
- For the future IVU designs a **length of the taper (or its angle)** is one of the key parameters of impedance evaluation. Its consideration was excluded from the present study because IVUs were already designed and installed



# 2. Impedance Evaluation for PF IVU

## Longitudinal Geometrical Impedance of Taper

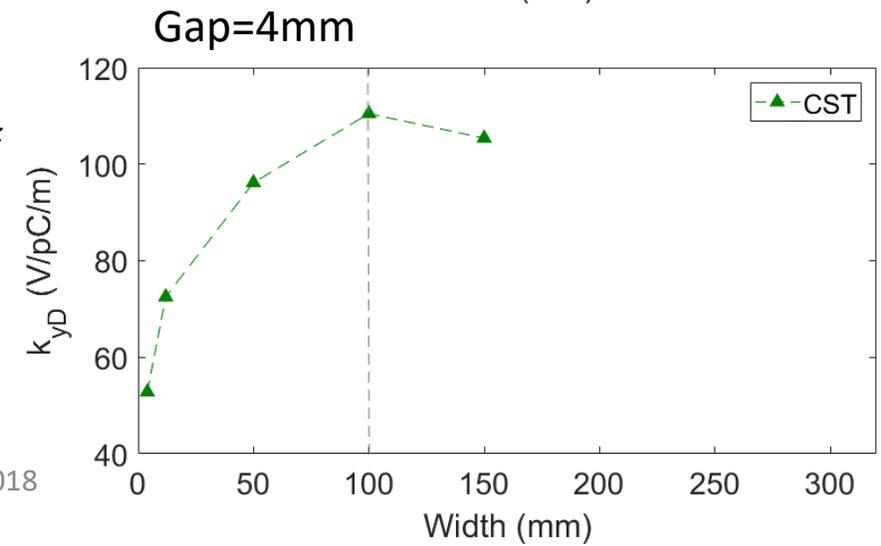
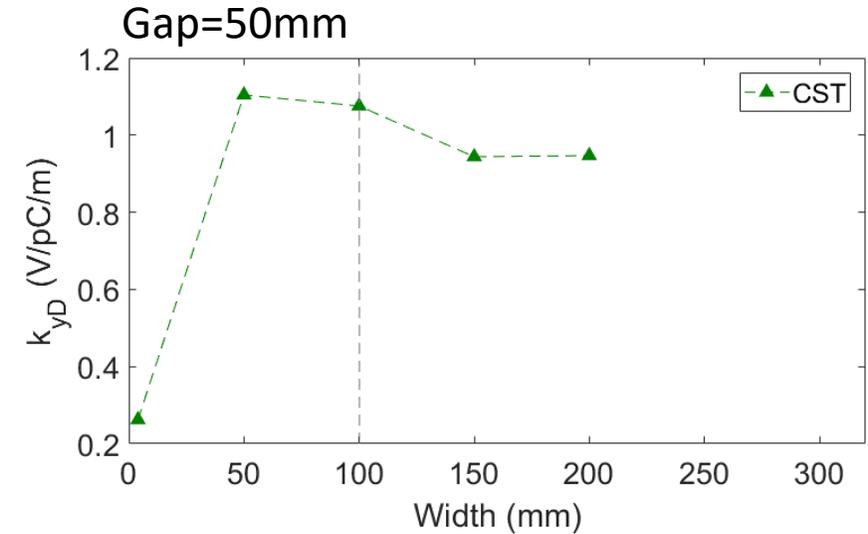
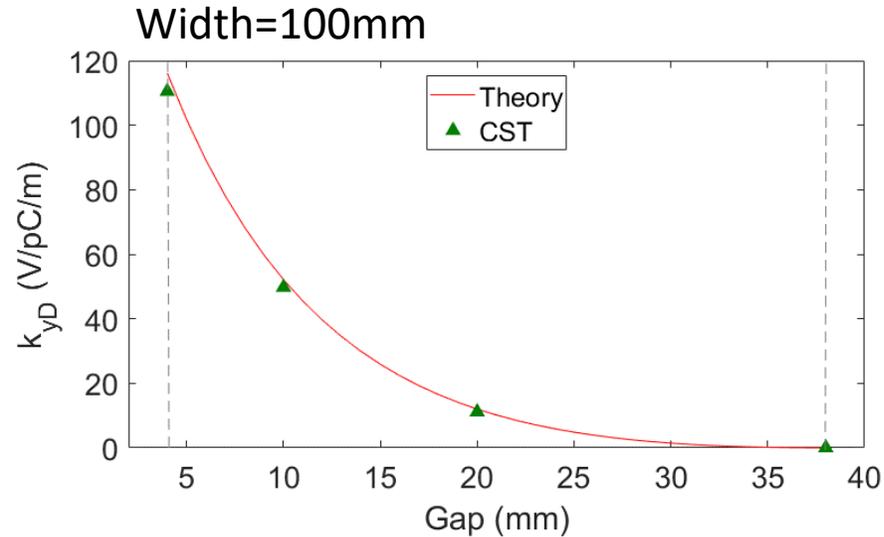


G. Stupakov 
$$\frac{Z_l}{n} = -i \frac{Z_0 \omega_0}{4\pi c} \int_{-\infty}^{\infty} (g')^2 F\left(\frac{g}{w}\right) dz, \quad b \ll w \ll l$$

$$F(x) = \sum_{m=0}^{\infty} \frac{1}{2m+1} \operatorname{sech}^2\left((2m+1)\frac{\pi x}{2}\right) \tanh\left((2m+1)\frac{\pi x}{2}\right).$$

# 2. Impedance Evaluation for PF IVU

## Dipolar Geometrical Impedance of Taper

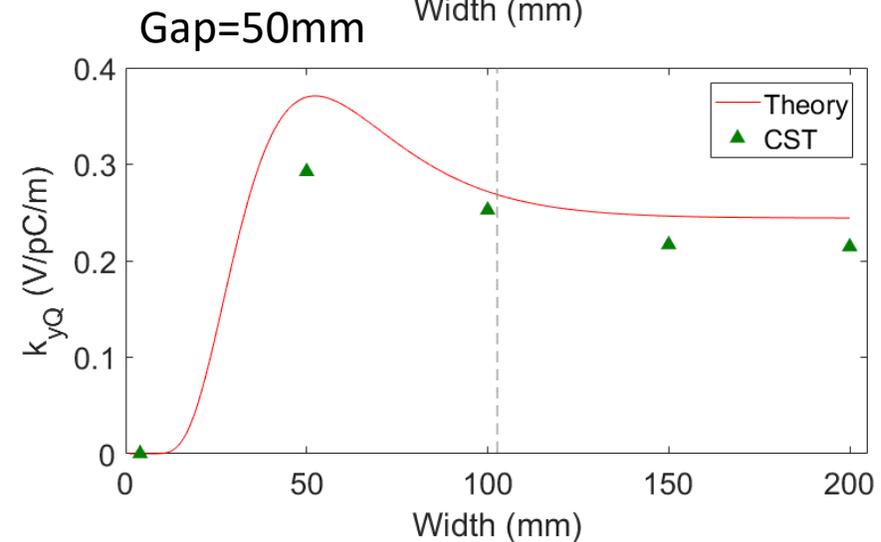
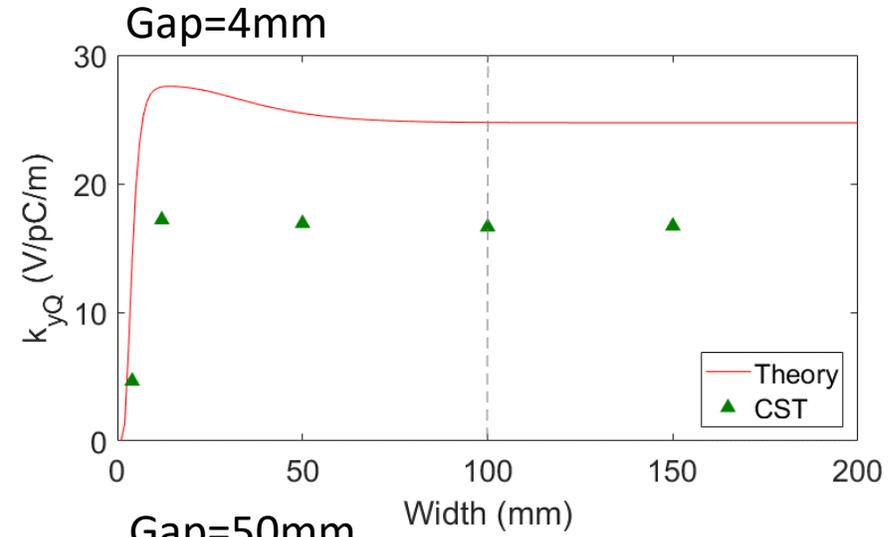
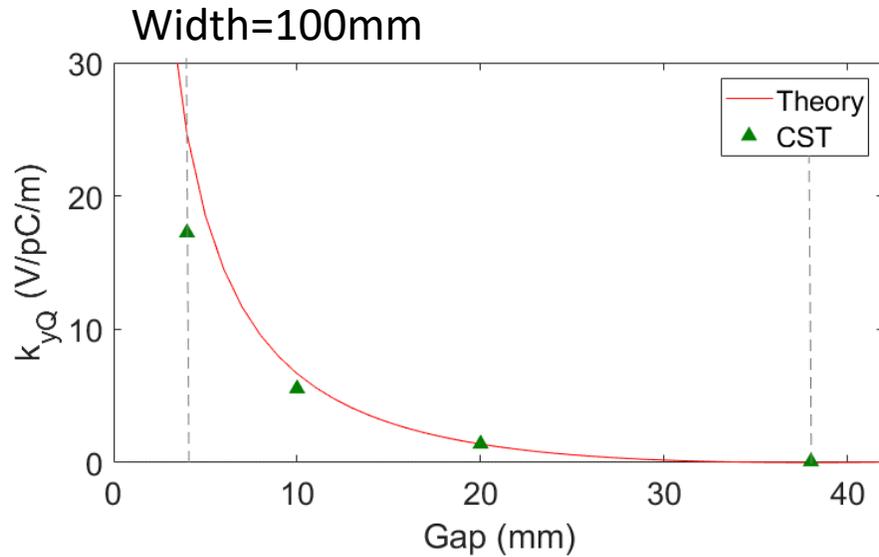


S. Krinsky  $Z_{yD}(k) = -i \frac{Z_0}{2\pi b} \int_{-\infty}^{\infty} \frac{\xi^2}{\sinh^2 \xi} \sum_{n=0}^{\infty} \delta_n \frac{H(k_n, k) + H(k_n, -k)}{2ik_n b} d\xi$

$H(p, k) = \int_{-\infty}^{\infty} \int_{-\infty}^{z_1} S'(z_1) S'(z_2) e^{i(p+k)(z_1-z_2)} dz_1 dz_2, \quad k_n b = \sqrt{(kb)^2 - \xi^2 - (\pi n)^2}$   
 $W \rightarrow \infty$

# 2. Impedance Evaluation for PF IVU

## Quadrupolar Geometrical Impedance of Taper



G. Stupakov

$$Z_{yQ} = -i \frac{\pi Z_0}{4} \int_{-\infty}^{\infty} \frac{(g')^2}{g^2} G\left(\frac{g}{w}\right) dz,$$

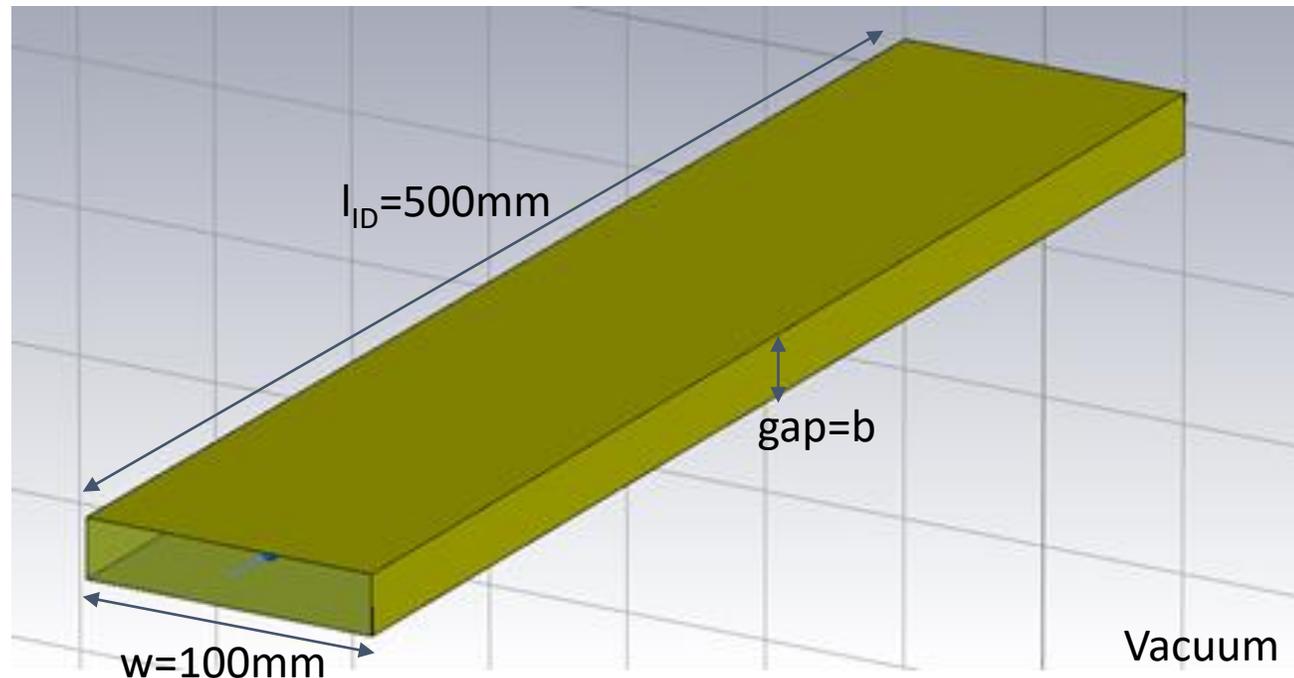
$$G(x) = x^2 \sum_{m=0}^{\infty} (2m+1) \times \operatorname{sech}^2\left((2m+1)\frac{\pi x}{2}\right) \tanh\left((2m+1)\frac{\pi x}{2}\right).$$

$$b \ll w \ll l$$

## 2. Impedance Evaluation for PF IVU

### Resistive-Wall Impedance of Undulator

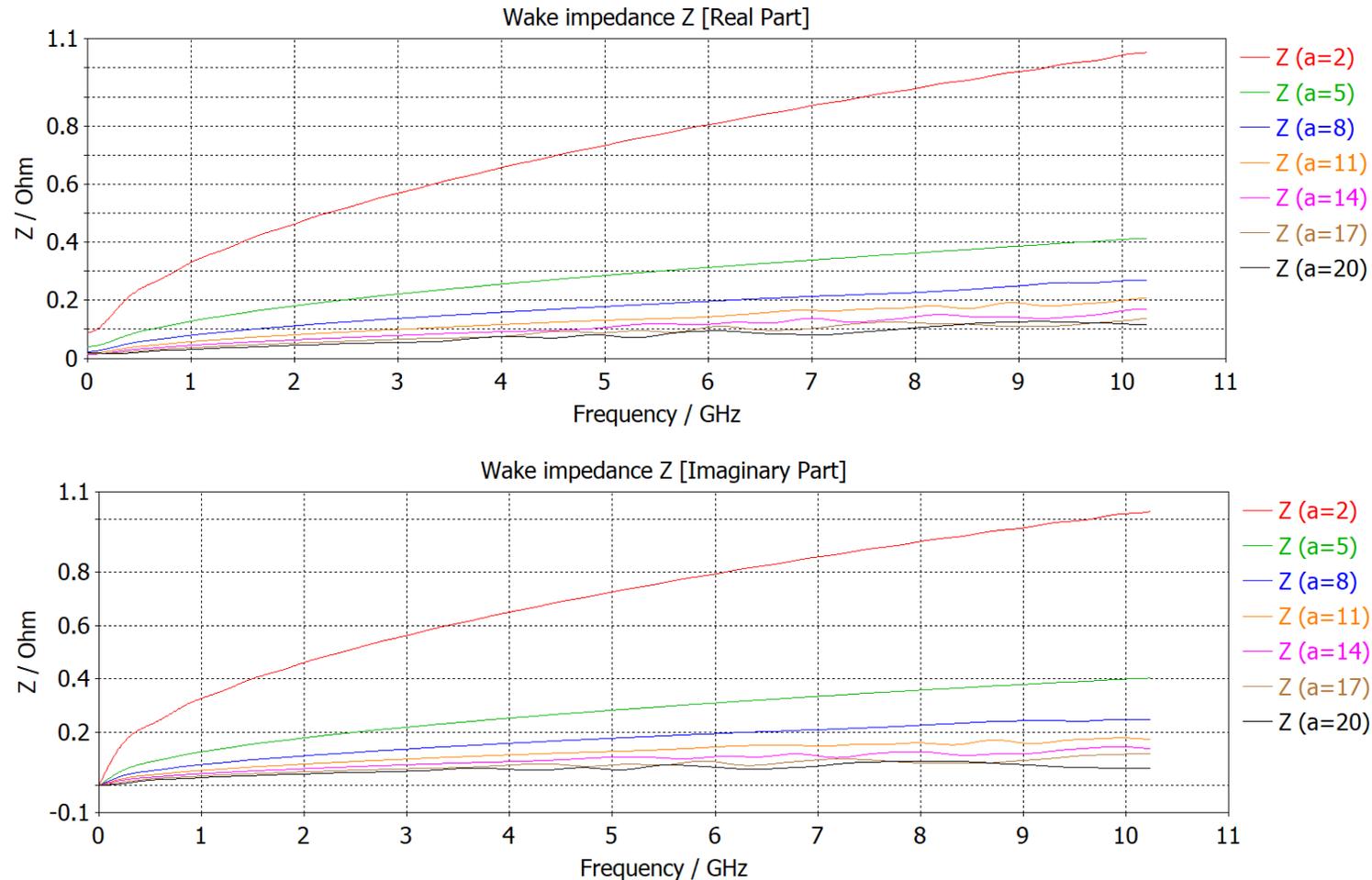
- By using the **copper resistivity** in CST, we can calculate the resistive impedance of the undulator with copper sheet



The electric conductivity of copper  $\sigma_c = 5.9 \times 10^7 \text{ S / m}$

# 2. Impedance Evaluation for PF IVU

## Longitudinal Resistive-Wall Impedance of Undulator



- The real and the imaginary parts of **longitudinal impedance** are identical as the theory shows:

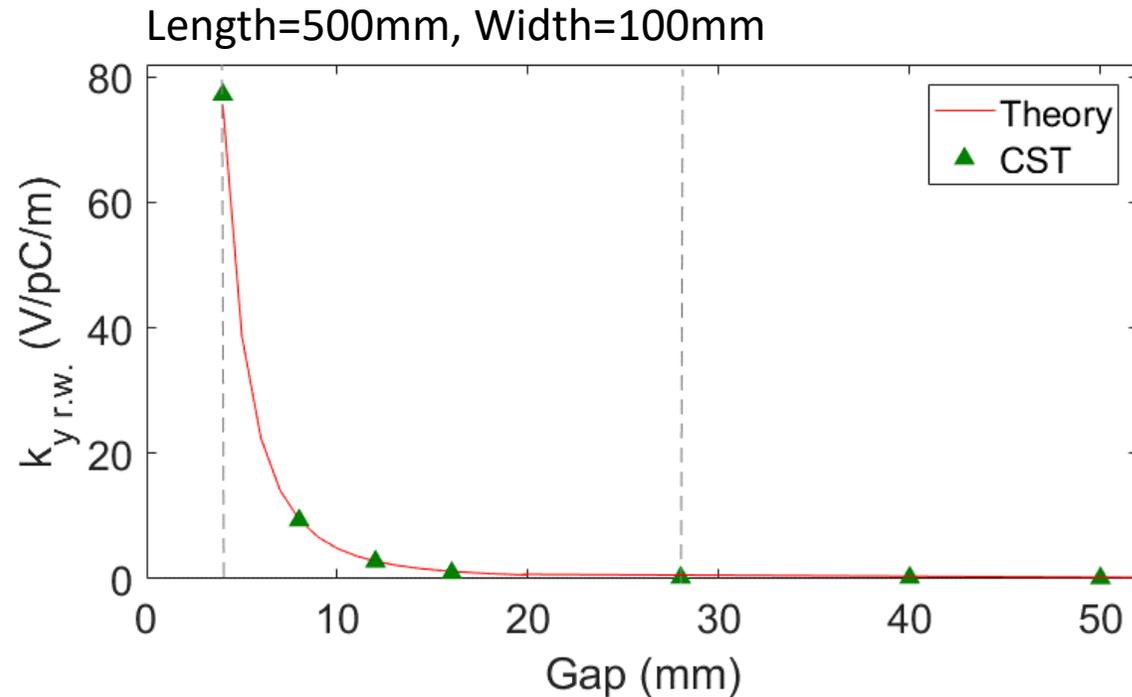
$$Z_{l.R.W.} = \frac{1 \pm i}{\pi b} \sqrt{\frac{\mu_r |\omega|}{2\sigma_c}} \left[ 1 + \frac{\pi y}{b} \tan\left(\frac{\pi y}{b}\right) \right]$$

A. Piwinski, Report No. DESY-94-068, 1994

It demonstrates that our CST Studio simulations are very accurate!

# 2. Impedance Evaluation for PF IVU

## Transverse Resistive-Wall Impedance of Undulator



O. Frasciello + V. Smaluk

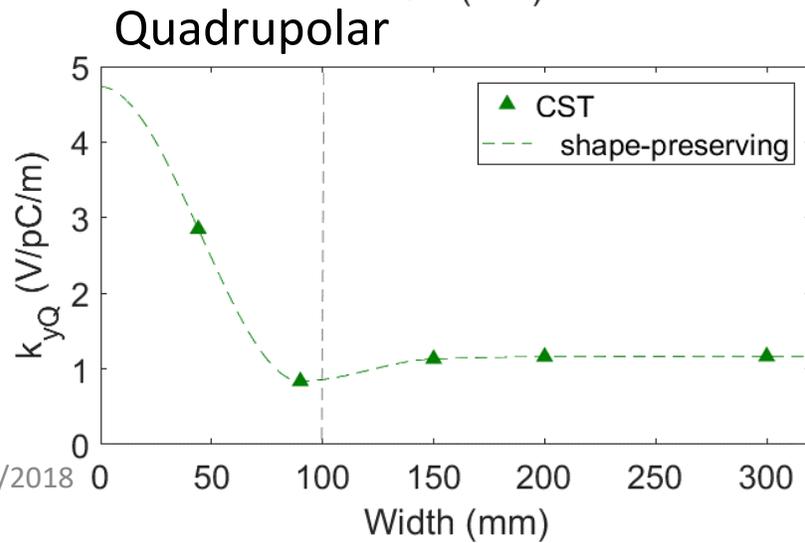
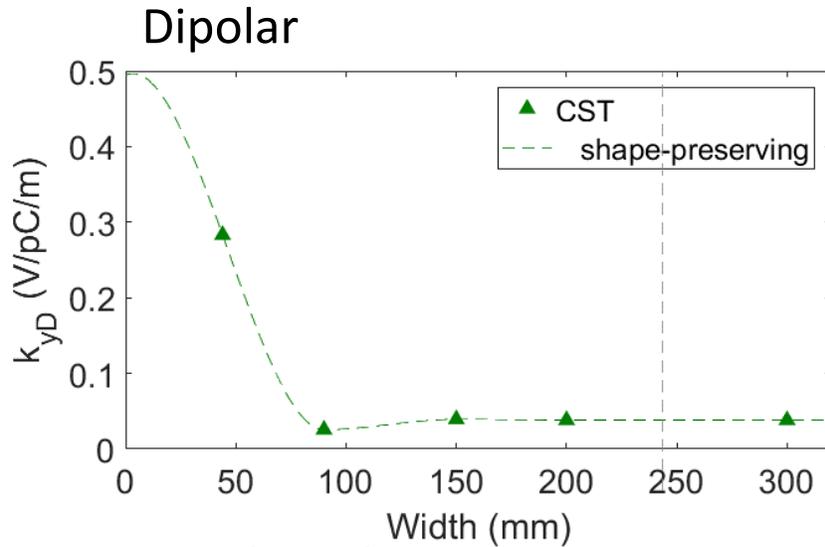
$$k_{yR.W.} = \frac{cL}{8b^3} \sqrt{\frac{2Z_0}{\sigma_z \sigma_c}} \Gamma\left(\frac{5}{4}\right)$$

L=Length of undulator

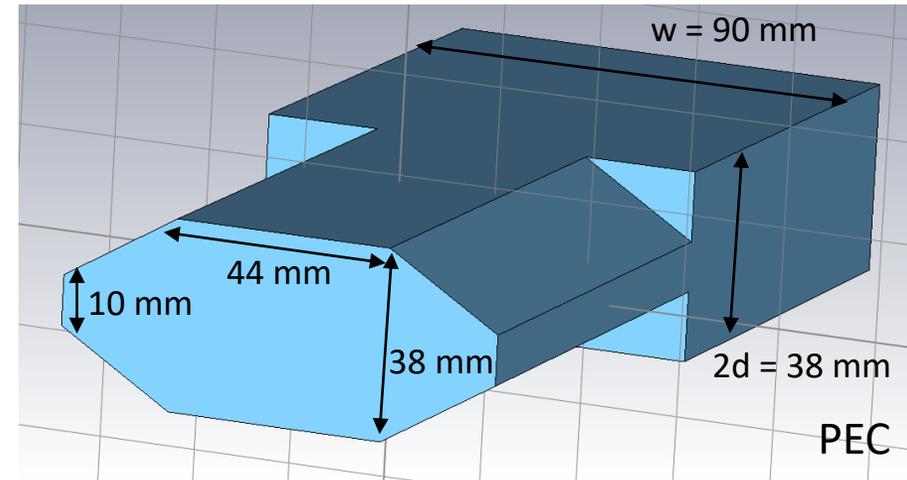
$$\Gamma\left(\frac{5}{4}\right) = 0.9064$$

# 2. Impedance Evaluation for PF IVU

## Geometrical Impedance of Step Transition



CST model of the step transition

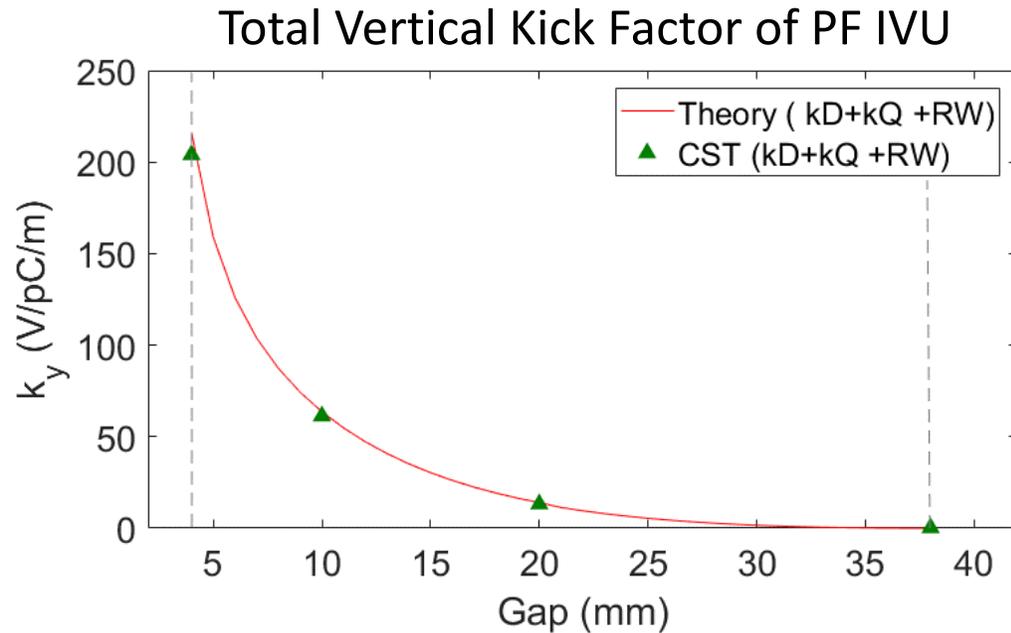


They have very small contributions to the total vertical kick factor and saturate at width = 150 mm

## 2. Impedance Evaluation for PF IVU

### Total Transverse Impedance of the IVU

- The total vertical kick factor due to 1 IVU is



Vertical kick factor per 1 IVU		CST PS	Theory
Taper vertical kick factor, V/pC/m	Dipolar	110.47	116.13
	Quadrupolar	16.64	24.61
Undulator vertical kick factor, V/pC/m	Dipolar	50.80	75.57
	Quadrupolar	26.40	
<b>Total vertical kick factor, V/pC/m</b>		<b>204.31</b>	<b>216.31</b>

- Impact of the step transition is three orders less, therefore is negligible

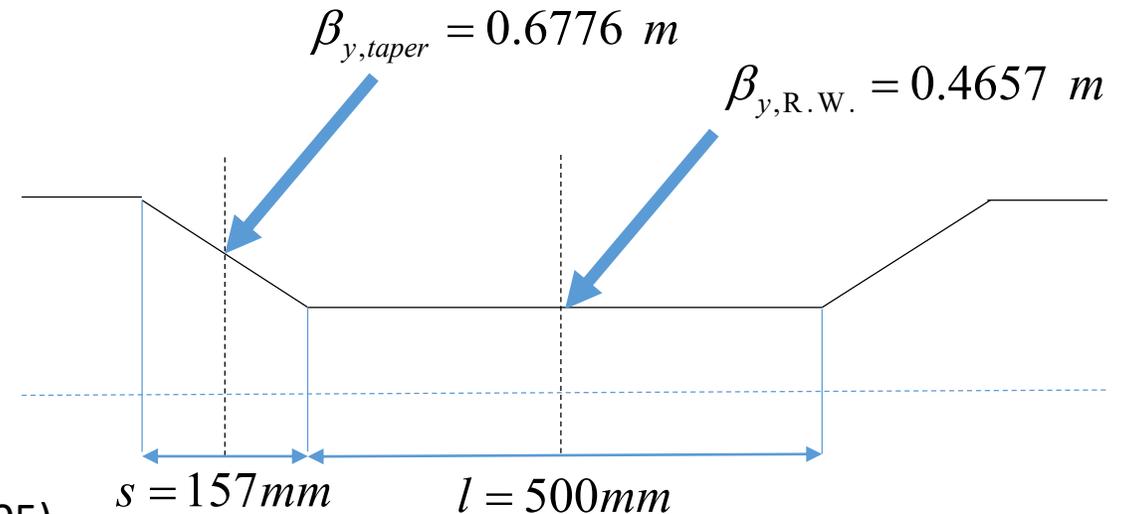
## 2. Impedance Evaluation for PF IVU

Additional Tune Shift by 4 IVU at PF (I)

- Tune shift per unit of bunch current caused by the IVU impedance can be estimated using formula:

$$\frac{\Delta \nu_y}{I_b} = -\frac{1}{4\pi(E/e)f_0} \sum_j \beta_{y,j} [k_{y,j}^{(1)} + k_{y,j}^{(2)}]$$

S. Sakanaka, et. al. Phys. Rev. ST Accel. Beams **8**, 042801 (2005)



- Average betatron function in the center of the undulator:

$$\langle \beta_{y,RW} \rangle = \beta_{y0} + (1 + \alpha_{y0}^2) l^2 / 12 / \beta_{y0} = 0.415 + (1 + 0.099^2) \times 0.5^2 / 12 / 0.415 = 0.4657 \text{ m}$$

- Average betatron function in the center of the taper:

$$\langle \beta_{y,taper} \rangle = \beta_{y0} + (1 + \alpha_{y0}^2) (s/2 + l/2)^2 / \beta_{y0} = 0.415 + (1 + 0.099^2) \times 0.3285^2 / 0.415 = 0.6776 \text{ m}$$

## 2. Impedance Evaluation for PF IVU

Additional Tune Shift by 4 IVU at PF (II)

- According to the CST simulations,

$$\begin{aligned}\frac{\Delta\nu}{I_b} &= -4 \times \langle \beta \times k_y \rangle / (4\pi f_0 (E/e)) = -0.488 \times 10^{15} / (4\pi \times 1.6 \times 10^6 \times 2.5 \times 10^9) = \\ &= -9.713 \times 10^{-6} \text{ (mA}^{-1}\text{)}\end{aligned}$$

- According to the theoretical formulas,

$$\begin{aligned}\frac{\Delta\nu}{I_b} &= -4 \times \langle \beta \times k_y \rangle / (4\pi f_0 (E/e)) = -0.522 \times 10^{15} / (4\pi \times 1.6 \times 10^6 \times 2.5 \times 10^9) = \\ &= -10.39 \times 10^{-6} \text{ (mA}^{-1}\text{)}\end{aligned}$$

# 2. Impedance Evaluation for PF IVU

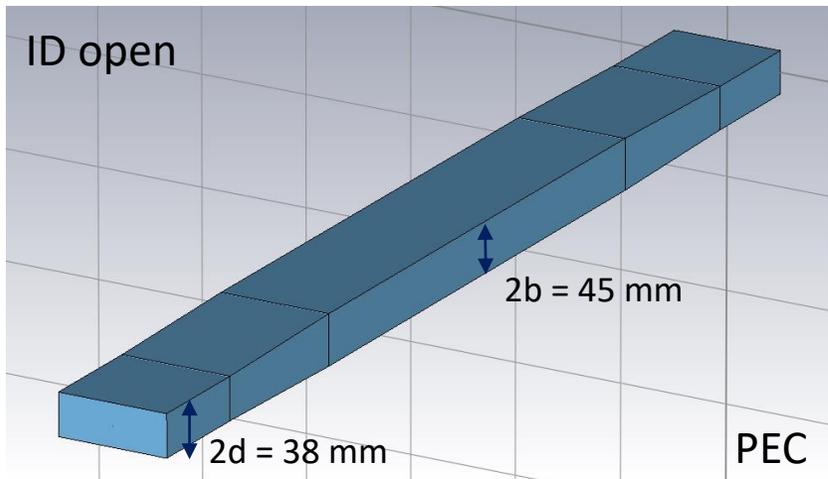
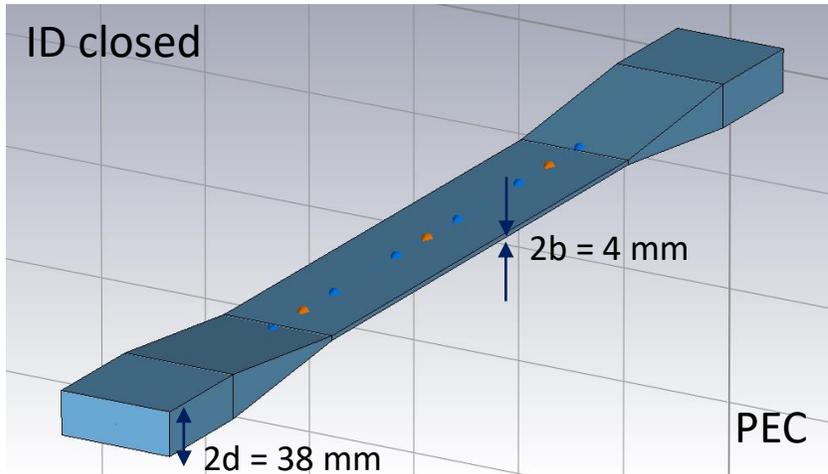
## Summary

- Excellent agreements between the theoretical predictions and CST Studio simulations for PF IVU
- Therefore, the new impedance evaluations of PF IVU are accurate enough in the framework of the theory and the simulation codes
- We can use these calculation results and computation resources and techniques for future impedance measurements, for the design of a new IVUs, and even for the impedance budget of the components of any new accelerator

# 3. Measurements of Kick Factors

# 3. Measurements of Kick Factors

## Tune Shift Measurement Method



- This additional tune shift corresponds to a difference of the vertical tune shifts for ID open (gap=45mm) and ID closed (gap=4mm) cases
- According to the CST simulations,

$$\begin{aligned}\frac{\Delta\nu}{I_b} &= -4 \times \langle \beta \times k_y \rangle / (4\pi f_0 (E/e)) \\ &= -0.488 \times 10^{15} / (4\pi \times 1.6 \times 10^6 \times 2.5 \times 10^9) \\ &= -9.713 \times 10^{-6} \text{ (mA}^{-1}\text{)}\end{aligned}$$

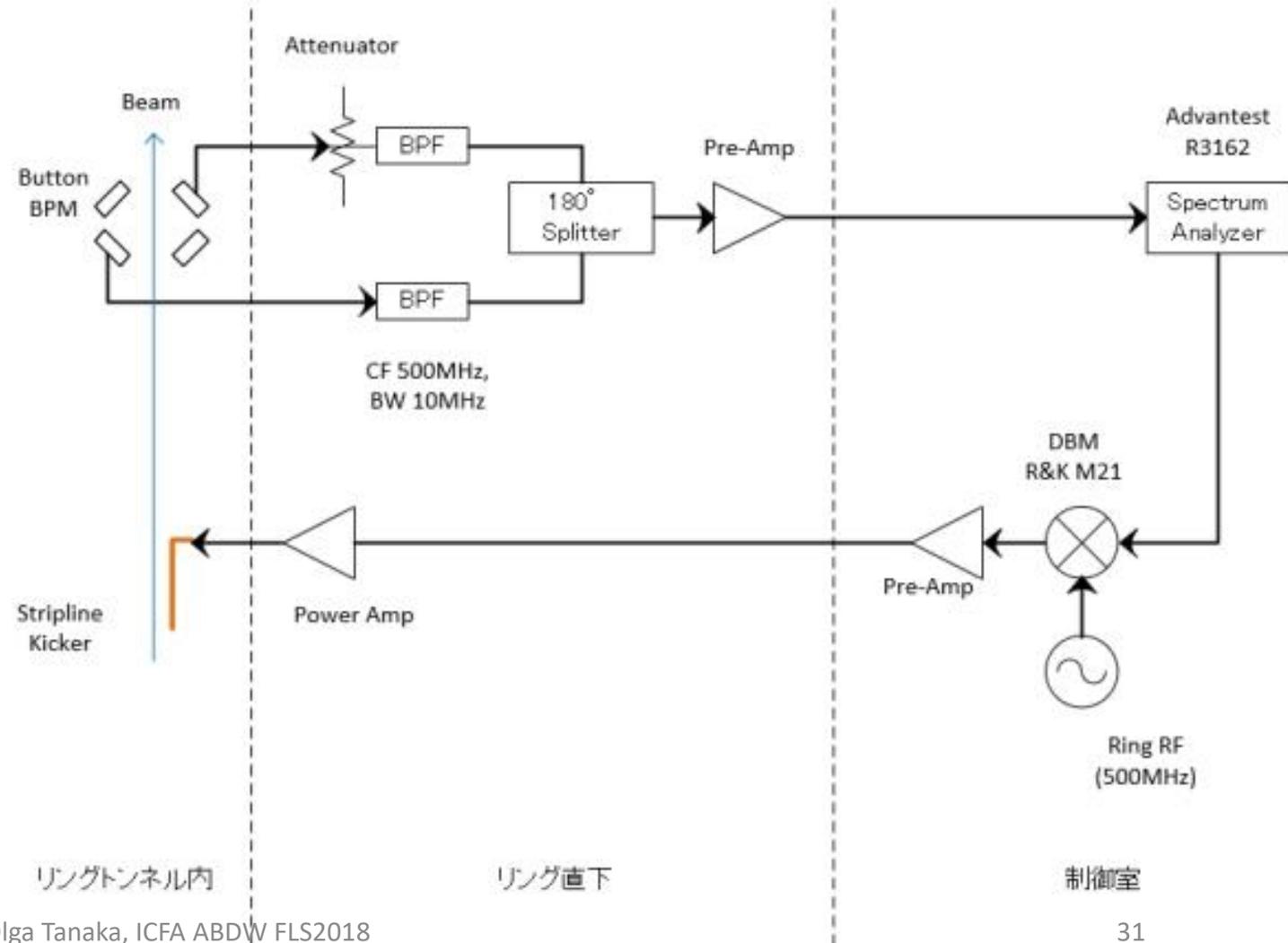
- According to the theoretical formulas,

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# 3. Measurements of Kick Factors

## RF Knock-Out

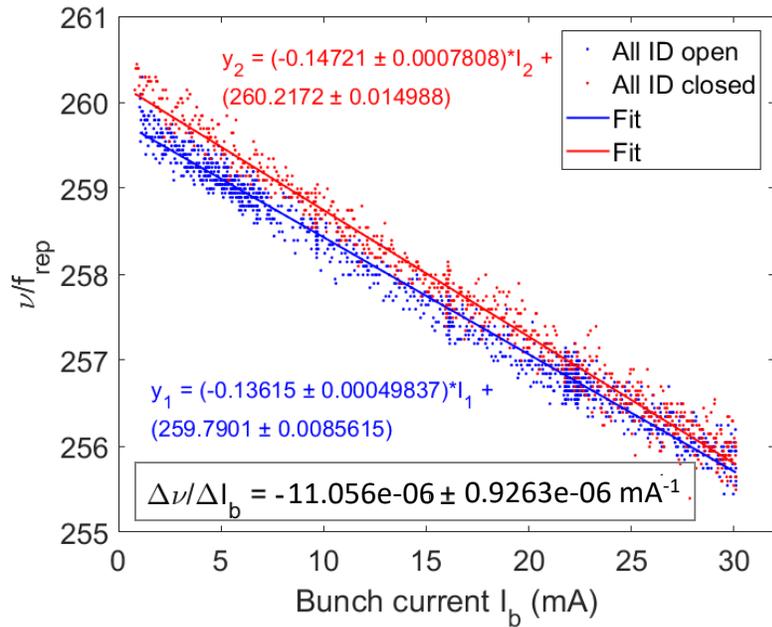
- Single bunch
- Feedback OFF
- The responses of the stripline kicker oscillations were measured by sweeping the bunch current (equal to changing the betatron frequency) using a spectrum analyzer equipped with a tracking generator.



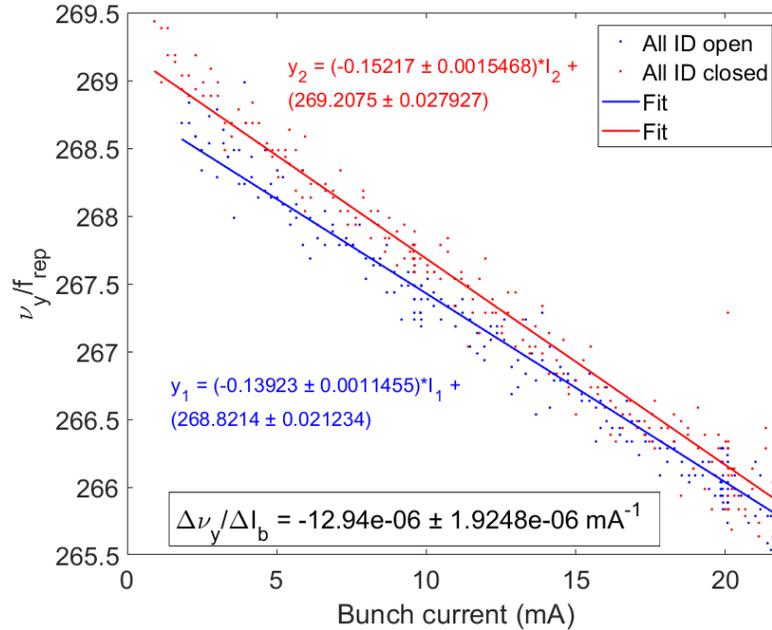
# 3. Measurements of Kick Factors

## Tune Shift Measurement Result

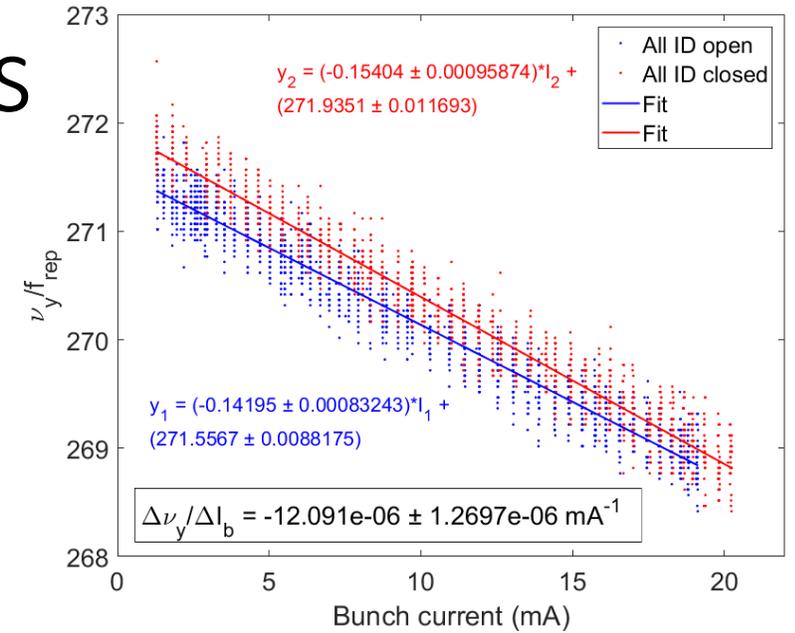
Measurement #1



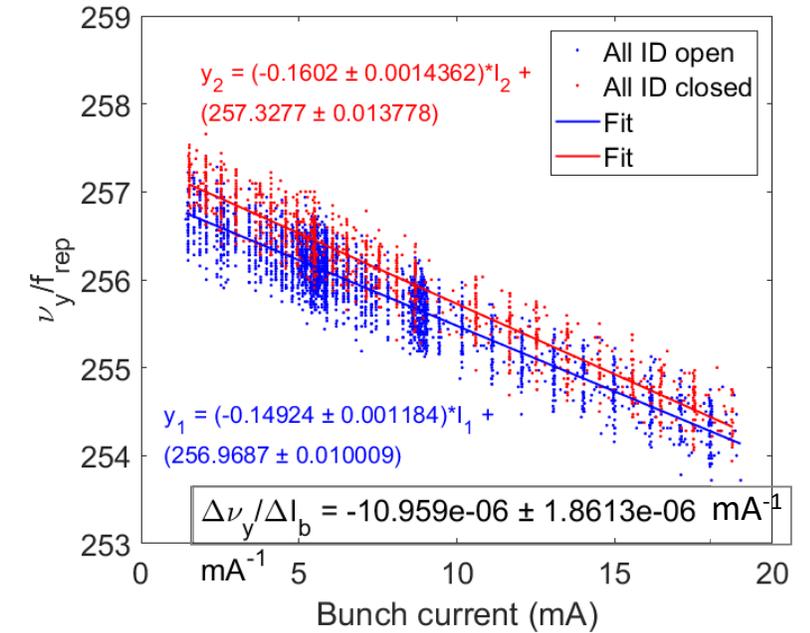
Measurement #2



Measurement #3



Measurement #4



	Theory	CST PS	Measurement (average)
Tune shift per bunch current ( $\text{mA}^{-1}$ )	$-10.39 \times 10^{-6}$	$-9.713 \times 10^{-6}$	$(-11.7615 \pm 1.4955) \times 10^{-6}$

Good agreement with our evaluations!

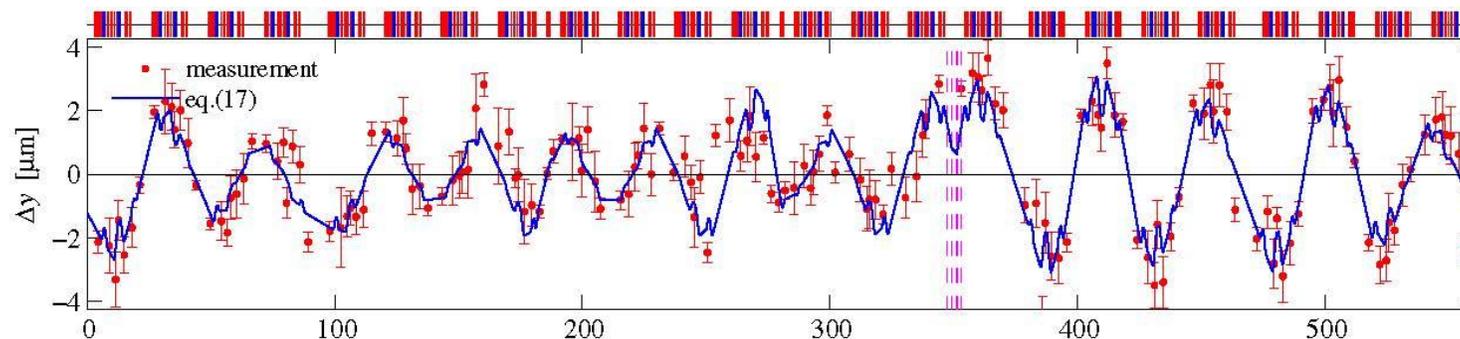
# 3. Measurements of Kick Factors

## Orbit Bump Measurement Method (I)

- Create an orbit bump at a location including IVU
- This orbit bump ( $y_0$ ) creates orbit deviations proportional to the kick factor of IVU along the ring:

$$\Delta y(s) = \frac{\Delta q}{E/e} k_y y_0 \frac{\sqrt{\beta(s)\beta(s_0)}}{2 \sin(\pi\nu)} \cos\left[|\mu(s) - \mu(s_0)| - \pi\nu\right],$$

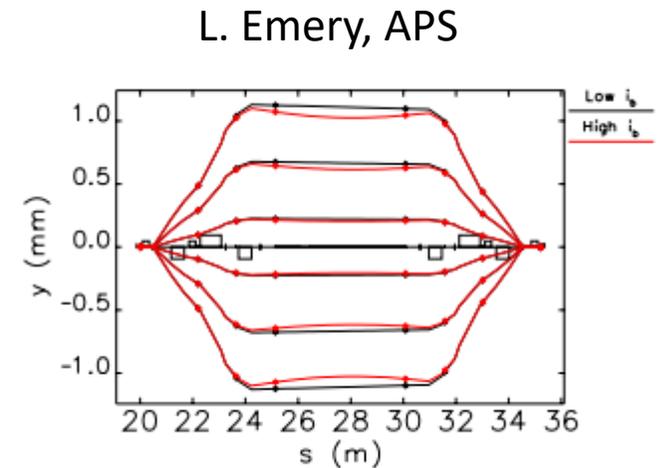
V. Smaluk, Phys. Rev. ST Accel. Beams 17, 074402 (2014)



# 3. Measurements of Kick Factors

## Orbit Bump Measurement Method (II)

- Measure the orbit deviations at many BPM positions to reduce statistical errors
- Repeat the above procedure for different orbit bumps and bunch charges to eliminate systematic errors caused by intensity dependent behavior of BPM electronics
- Using the analytical formula and the Twiss parameters of the ring, we can identify the kick factor of IVU
- The measurement is scheduled in April



# Summary

- We have identified the **major impedance contributors of PF IVU** and successfully evaluated their impedance using theoretical formulas, CST Studio simulations and measurements
- The three evaluations show **very good agreements**
- The established methods and procedure will greatly help the **design of future IVU** for further reduction of impedance

Thank you for your attention!

# Backup

# Possible reasons of the difference in estimated and measured tune shift values

- 1. Size of the gap between two copper shields (3.83 mm vs 4 mm)**
- 2. Thickness of the copper shield is not enough**
3. Difference in present and model values of betatron function
4. Difference in values of betatron function when ID gap is opened/closed
5. Reliability of CST code
6. Accuracy of the tune shift measurement

Courtesy of N. Nakamura

# 1. Size of the gap between two copper shields

- The smallest ID gap  $g = 2b = 4 \text{ mm}$  ( $b = 2 \text{ mm}$ )
- The smallest ID gap  $g = 2b = 4 \text{ mm}$  ( $b = 2 \text{ mm}$ )
- Thickness of the shield  $t = 60 \text{ mm (Cu)} + 25 \text{ mm (Ni)} = 85 \text{ mm}$
- Real size of the gap  $g_s = 2b_s = 4 - 0.085 \times 2 = 3.83 \text{ mm}$  ( $b_s = 1.915 \text{ mm}$ )
- Resistive-wall impedance(imaginary part) & kick factor

$$\text{Im } Z_y(f) \approx -\frac{\pi Z_0 L}{16b_s^3} \sqrt{\frac{1}{\pi |f| \mu_0 \sigma_{Cu}}}$$

$$k_y = f_0 \sum_{p=-\infty}^{\infty} \text{Im } Z_{Dy}(pf_0 + f_\beta) h(pf_0 + f_\beta)$$

$$\left( h(\omega) = \exp\left\{-\left(\omega \sigma_z / c\right)^2\right\} \right)$$



$$k_y = 85.97 \text{ V / pC / m } (f = -10 \sim +10 \text{ GHz})$$

$$cf. k_y(b = 4\text{mm}) = 75.46 \text{ V / pC / m}$$

**Influence of about 14%**

Courtesy of N. Nakamura

## 2. Thickness of the copper shield is not enough

- Frequency at which copper skin depth and copper sheet thickness are the same ( $\delta_{Cu} = d_{Cu}$ )  $d_{Cu} = d_{Cu} \left( d_{Cu} = \sqrt{\frac{1}{\rho S_{Cu} m_0 |f| j}} \right) \rightarrow f_{\delta} = \frac{1}{\pi \sigma_{Cu} \mu_0 d_{Cu}^2}$
- Resistive-wall impedance formula (switched by frequency)

$$|f| \geq f_{\delta} = \frac{1}{\pi \sigma_{Cu} \mu_0 d_{Cu}^2} = 1.19 \text{ MHz} (d_{Cu} = 60 \mu\text{m}) \rightarrow \text{Im} Z_y(f) \approx -\frac{\pi Z_0 L}{16b^3} \sqrt{\frac{1}{\pi |f| \mu_0 \sigma_{Cu}}}$$

$$|f| < f_{\delta} (f = \Delta \nu_{\beta} f_0, f = -(1 - \Delta \nu_{\beta}) f_0) \rightarrow \text{Im} Z_y(f) \approx -\frac{\pi Z_0 L}{16b^3} \sqrt{\frac{1}{\pi |f| \mu_0 \sigma_{NdFeB}}}$$

$$(S_{NdFeB} = 0.6 \times 10^6 \text{ W}^{-1} \text{m}^{-1}, S_{Ni} = 14 \times 10^6 \text{ W}^{-1} \text{m}^{-1})$$

$$k_y = f_0 \sum_{p=-\infty}^{\infty} \text{Im} Z_y(pf_0 + f_{\beta}) h(pf_0 + f_{\beta})$$

$$k_y = 86.04 \text{ V / pC / m} (f = -10 \sim +10 \text{ GHz}) \text{ cf. } k_y(\text{Cu}) = 75.46 \text{ V / pC / m}$$

Courtesy of N. Nakamura

**Influence of about 14%**